

60 V, P-channel Trench MOSFET

16 April 2020

**Product data sheet** 

### 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

#### 3. Applications

- Relay driver
- High-speed line driver
- High-side load switch
- Switching circuits

#### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions   |     | Min | Тур | Мах  | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|------|------|
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -   | -60  | V    |
| V <sub>GS</sub>   | gate-source voltage              |  |     | -20 | -   | 20   | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C                        | [1] | -   | -   | -2.2 | А    |
| Static chara      | octeristics                      |  |     |     |     |      |      |
| R <sub>DSon</sub> | drain-source on-state resistance | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -2.2 A; T <sub>j</sub> = 25 °C |     | -   | 100 | 130  | mΩ   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

### 5. Pinning information

#### Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | G      | gate        | 3                  | D              |
| 2   | S      | source      |                    |                |
| 3   | D      | drain       |                    | G              |
|     |        |             |                    | S<br>017aaa094 |
|     |        |             | SOT23              |                |

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#### 6. Ordering information

| Table 3. Ordering information |         |  |         |  |  |  |
|-------------------------------|---------|--|---------|--|--|--|
| Type number                   | Package |  |         |  |  |  |
|                               | Name    | Description  | Version |  |  |  |
| PMV100EPA                     | SOT23   | plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body | SOT23   |  |  |  |

#### 7. Marking

| Table 4. Marking codes |                 |
|------------------------|-----------------|
| Type number            | Marking code[1] |
| PMV100EPA              | %GP             |

[1] % = placeholder for manufacturing site code

#### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

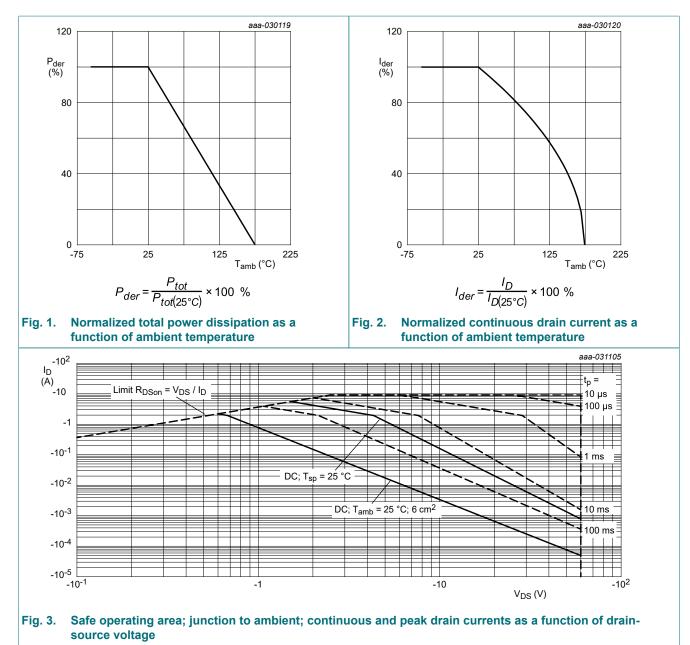
| Symbol               | Parameter  | Conditions  |     | Min | Мах  | Unit |
|----------------------|--|---|-----|-----|------|------|
| V <sub>DS</sub>      | drain-source voltage                             | T <sub>j</sub> = 25 °C  |     | -   | -60  | V    |
| V <sub>GS</sub>      | gate-source voltage                              |   |     | -20 | 20   | V    |
| ID                   | drain current                                    | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C   | [1] | -   | -2.2 | А    |
|                      |  | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C  | [1] | -   | -1.4 | А    |
| I <sub>DM</sub>      | peak drain current                               | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$                                       |     | -   | -9   | Α    |
| P <sub>tot</sub>     | total power dissipation                          | T <sub>amb</sub> = 25 °C  | [2] | -   | 710  | mW   |
|                      |  |   | [1] | -   | 1.3  | W    |
|                      |  | T <sub>sp</sub> = 25 °C   |     | -   | 8.3  | W    |
| Tj                   | junction temperature                             |   |     | -55 | 175  | °C   |
| T <sub>amb</sub>     | ambient temperature                              |   |     | -55 | 175  | °C   |
| T <sub>stg</sub>     | storage temperature                              |   |     | -65 | 175  | °C   |
| Source-drai          | n diode  |   |     | I   |      |      |
| I <sub>S</sub>       | source current                                   | T <sub>amb</sub> = 25 °C  | [1] | -   | -1.4 | А    |
| ESD maxim            | um rating  |   |     |     |      |      |
| V <sub>ESD</sub>     | electrostatic discharge voltage                  | НВМ   | [3] | -   | 400  | V    |
| Avalanche r          | uggedness  |   |     |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche energy | $ T_{j(init)} = 25 \text{ °C}; I_D = -1 \text{ A}; \text{ DUT in avalanche}$<br>(unclamped) |     | -   | 33   | mJ   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint. [2]

[3] Measured between all pins.

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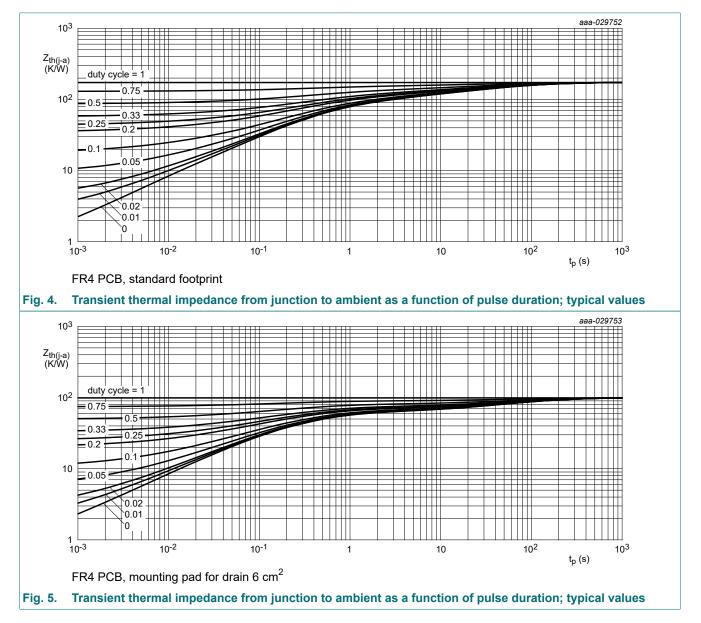


### 9. Thermal characteristics

| Symbol   | Parameter  | Conditions  |     | Min | Тур | Мах | Unit |
|--|--|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> thermal resistance from junction to ambient | thermal resistance from                          | in free air | [1] | -   | 175 | 210 | K/W  |
|  |  | [2]         | -   | 95  | 115 | K/W |      |
| R <sub>th(j-sp)</sub>  | thermal resistance from junction to solder point |             |     | -   | 13  | 18  | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

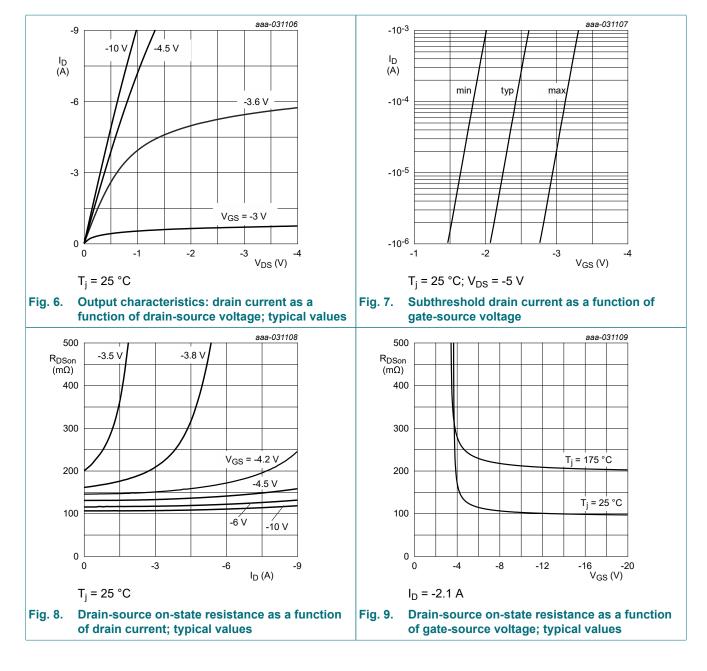
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



### **10. Characteristics**

| Symbol               | Parameter                         | Conditions  | Min  | Тур  | Max  | Unit |
|----------------------|-----------------------------------|---|------|------|------|------|
| Static chara         | cteristics                        |   |      |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage | I <sub>D</sub> = -250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -60  | -    | -    | V    |
| V <sub>GSth</sub>    | gate-source threshold voltage     | $I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C                      | -1.9 | -2.5 | -3.2 | V    |
| I <sub>DSS</sub>     | drain leakage current             | V <sub>DS</sub> = -60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -    | -    | -1   | μA   |
| I <sub>GSS</sub>     | gate leakage current              | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -    | -    | -100 | nA   |
|                      |                                   | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -    | -    | 100  | nA   |
| R <sub>DSon</sub>    | drain-source on-state             | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -2.2 A; T <sub>j</sub> = 25 °C  | -    | 100  | 130  | mΩ   |
|                      | resistance                        | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -2.2 A; T <sub>j</sub> = 175 °C | -    | 212  | 276  | mΩ   |
|                      |                                   | V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -1.8 A; T <sub>j</sub> = 25 °C | -    | 130  | 180  | mΩ   |
| 9 <sub>fs</sub>      | forward<br>transconductance       | V <sub>DS</sub> = -10 V; I <sub>D</sub> = -2.1 A; T <sub>j</sub> = 25 °C  | -    | 6    | -    | S    |
| R <sub>G</sub>       | gate resistance                   | f = 1 MHz   | -    | 11   | -    | Ω    |
| Dynamic ch           | aracteristics                     |   |      |      |      |      |
| Q <sub>G(tot)</sub>  | total gate charge                 | $V_{DS}$ = -30 V; $I_{D}$ = -2.1 A; $V_{GS}$ = -10 V;                     | -    | 11   | 17   | nC   |
| Q <sub>GS</sub>      | gate-source charge                | T <sub>j</sub> = 25 °C  | -    | 1.9  | -    | nC   |
| Q <sub>GD</sub>      | gate-drain charge                 |   | -    | 2.4  | -    | nC   |
| C <sub>iss</sub>     | input capacitance                 | V <sub>DS</sub> = -30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                | -    | 616  | -    | pF   |
| C <sub>oss</sub>     | output capacitance                | T <sub>j</sub> = 25 °C  | -    | 41   | -    | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance      |   | -    | 26   | -    | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                | $V_{DS}$ = -30 V; I <sub>D</sub> = -2.1 A; V <sub>GS</sub> = -10 V;       | -    | 7    | -    | ns   |
| t <sub>r</sub>       | rise time                         | R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C                         | -    | 7    | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time               | 1   | -    | 29   | -    | ns   |
| t <sub>f</sub>       | fall time                         | 1   | -    | 25   | -    | ns   |
| Source-drai          | n diode                           |   |      |      |      |      |
| V <sub>SD</sub>      | source-drain voltage              | I <sub>S</sub> = -1.4 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -    | -0.8 | -1.2 | V    |
| t <sub>rr</sub>      | reverse recovery time             | I <sub>S</sub> = -1.4 A; dI <sub>S</sub> /dt = 100 A/μs;                  | -    | 18   | -    | ns   |
| Q <sub>r</sub>       | recovered charge                  | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = -30 V; T <sub>j</sub> = 25 °C    | -    | 13   | -    | nC   |

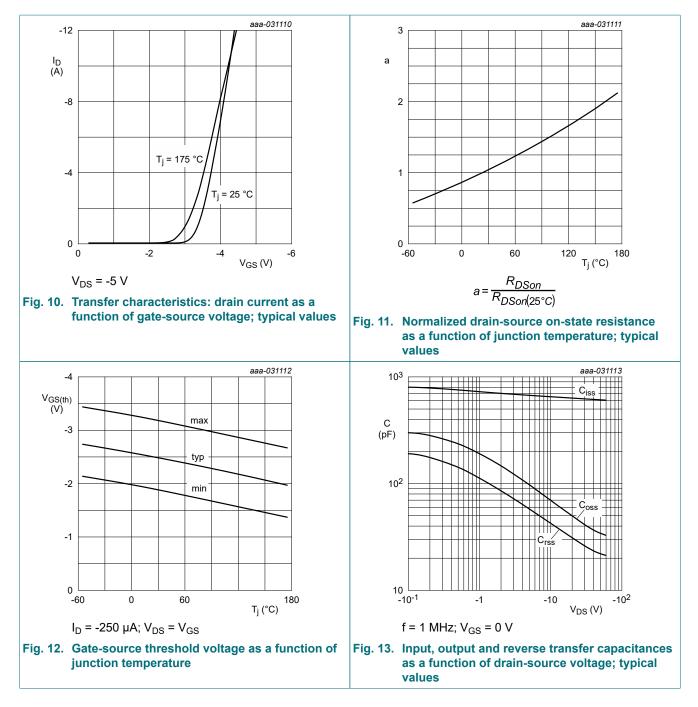
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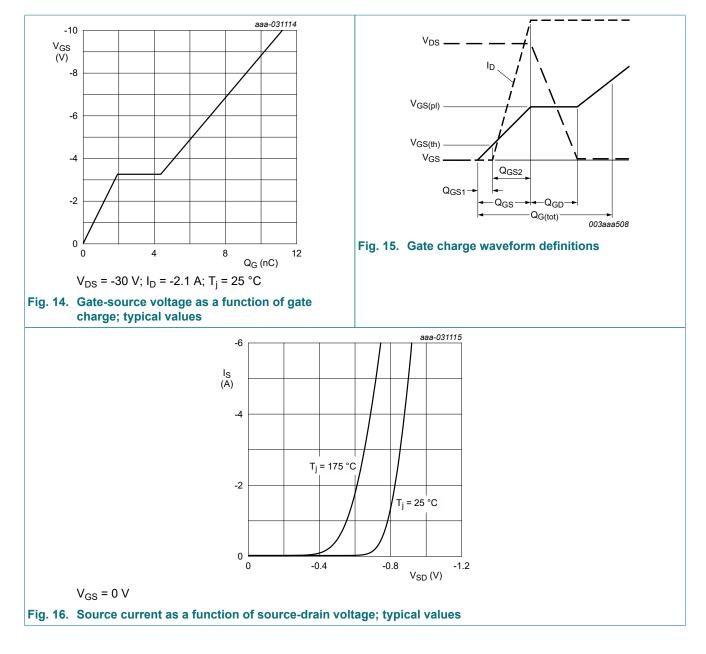
**Product data sheet** 

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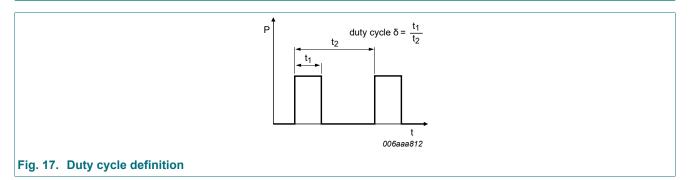
#### 60 V, P-channel Trench MOSFET



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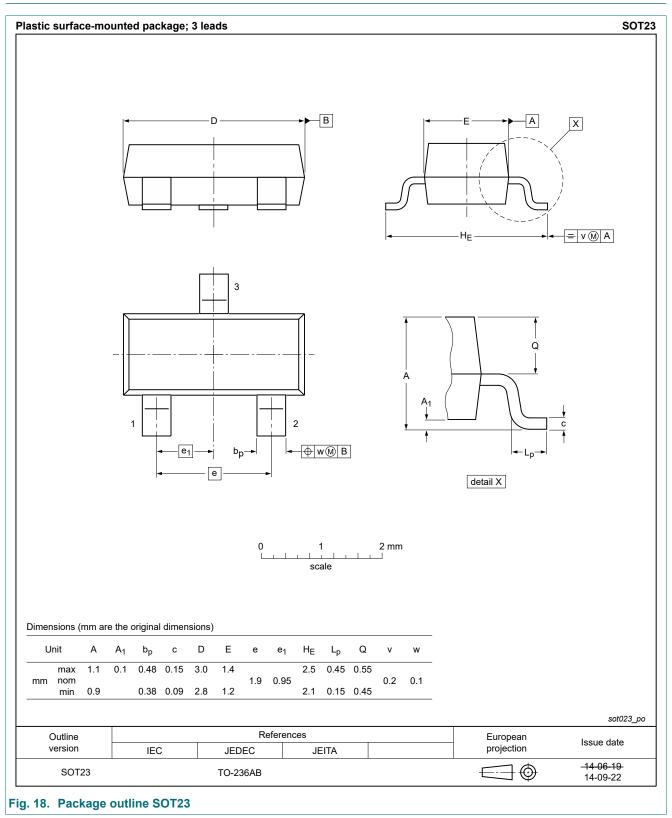
### **11. Test information**



#### **Quality information**

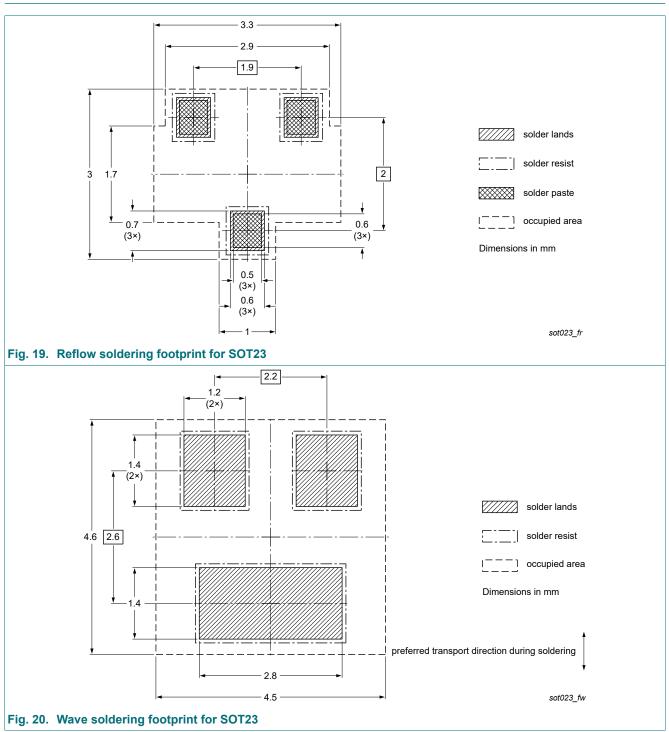
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



#### 60 V, P-channel Trench MOSFET

### 13. Soldering



### 14. Revision history

| Table 8. Revision history |              |                    |               |            |  |  |
|---------------------------|--------------|--------------------|---------------|------------|--|--|
| Data sheet ID             | Release date | Data sheet status  | Change notice | Supersedes |  |  |
| PMV100EPA v.1             | 20200416     | Product data sheet | -             | -          |  |  |

#### 60 V, P-channel Trench MOSFET

#### 15. Legal information

#### Data sheet status

| Document status<br>[1][2]         | Product<br>status [3] | Definition  |
|-----------------------------------|-----------------------|---|
| Objective [short]<br>data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short]<br>data sheet | Qualification         | This document contains data from the preliminary specification.                       |
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